

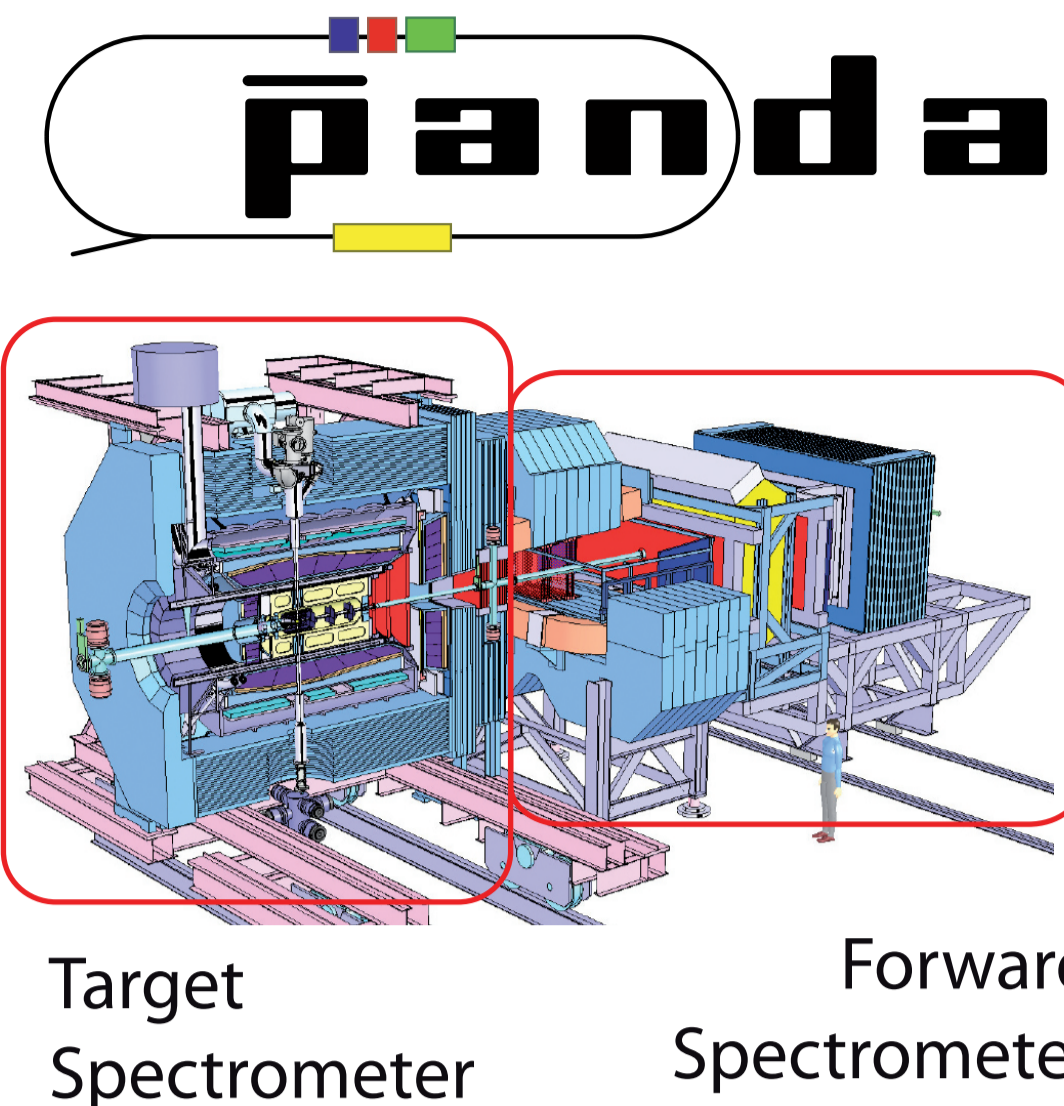
Triggerless readout for silicon detectors at PANDA

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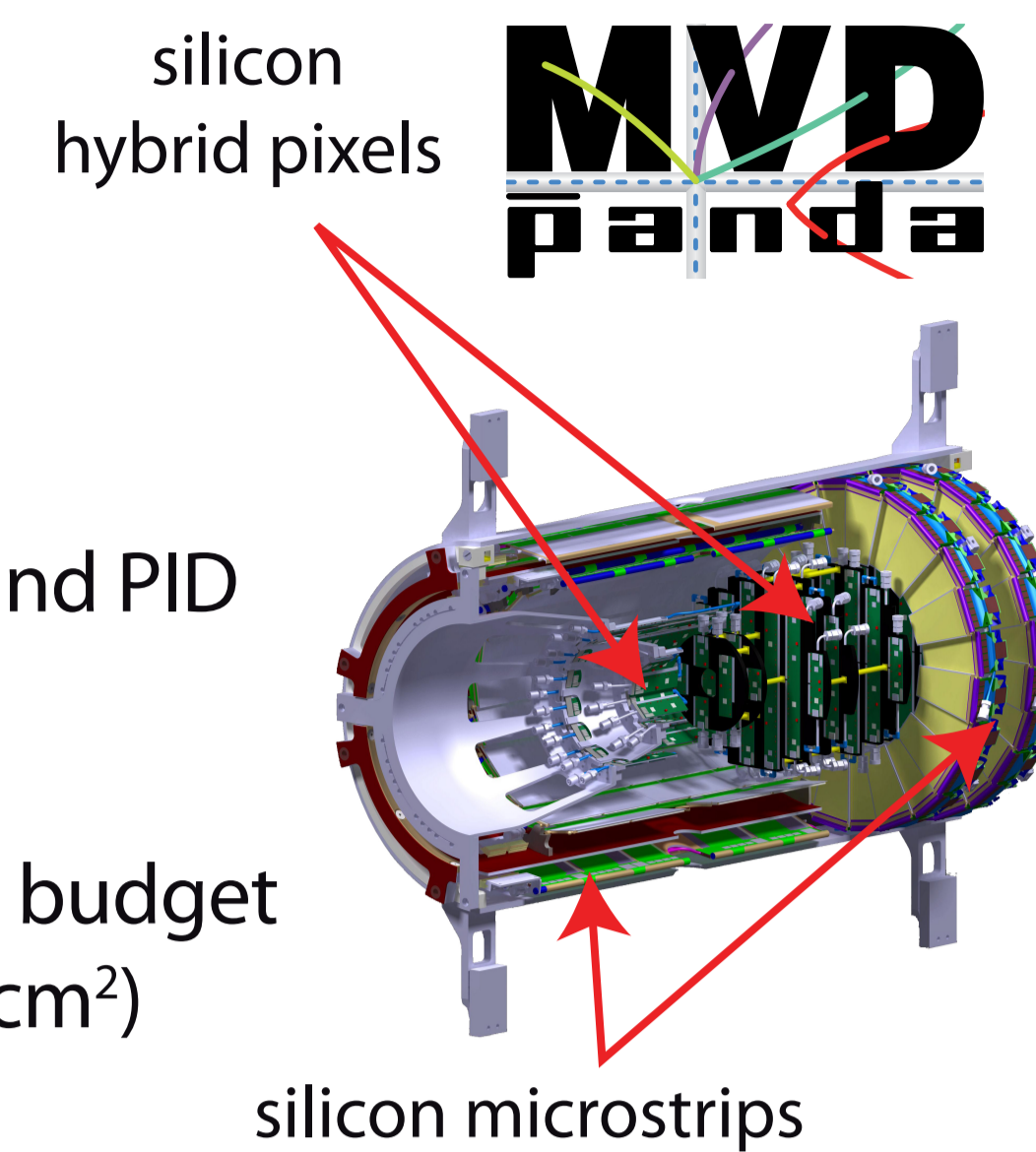
The PANDA Experiment

- Fixed target experiment
- Almost 4π acceptance
- Cooled antiproton beam using electron and stochastic cooling
- Proton or heavy nuclear target
- Momentum from 1.5 up to 15 GeV/c
- Trigger-less readout at $\sim 10^7$ interactions / s



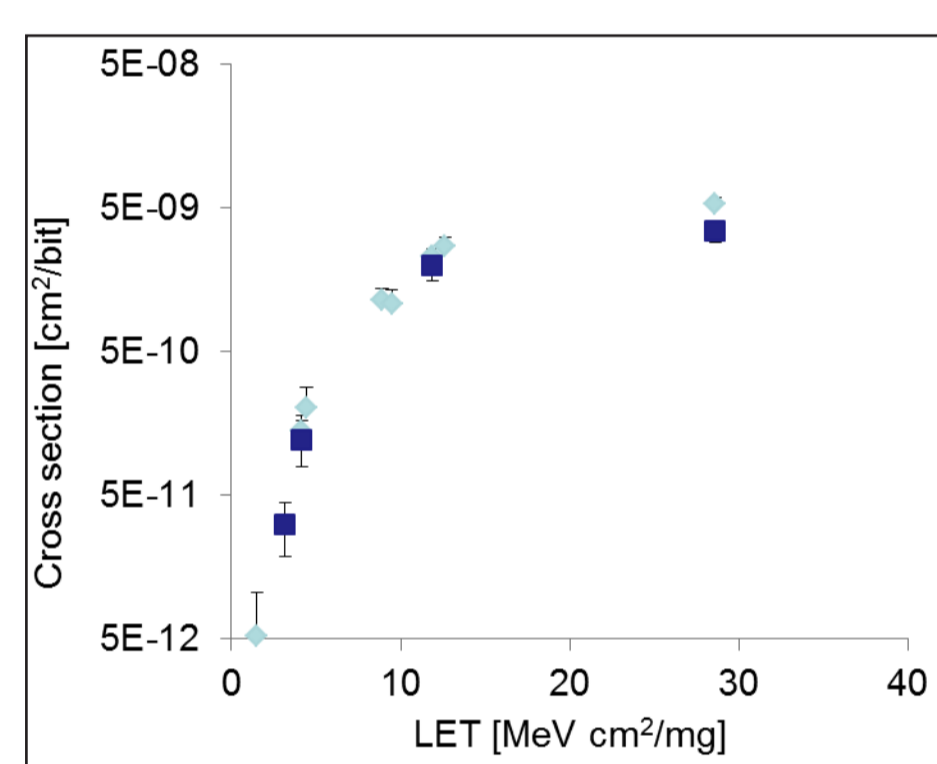
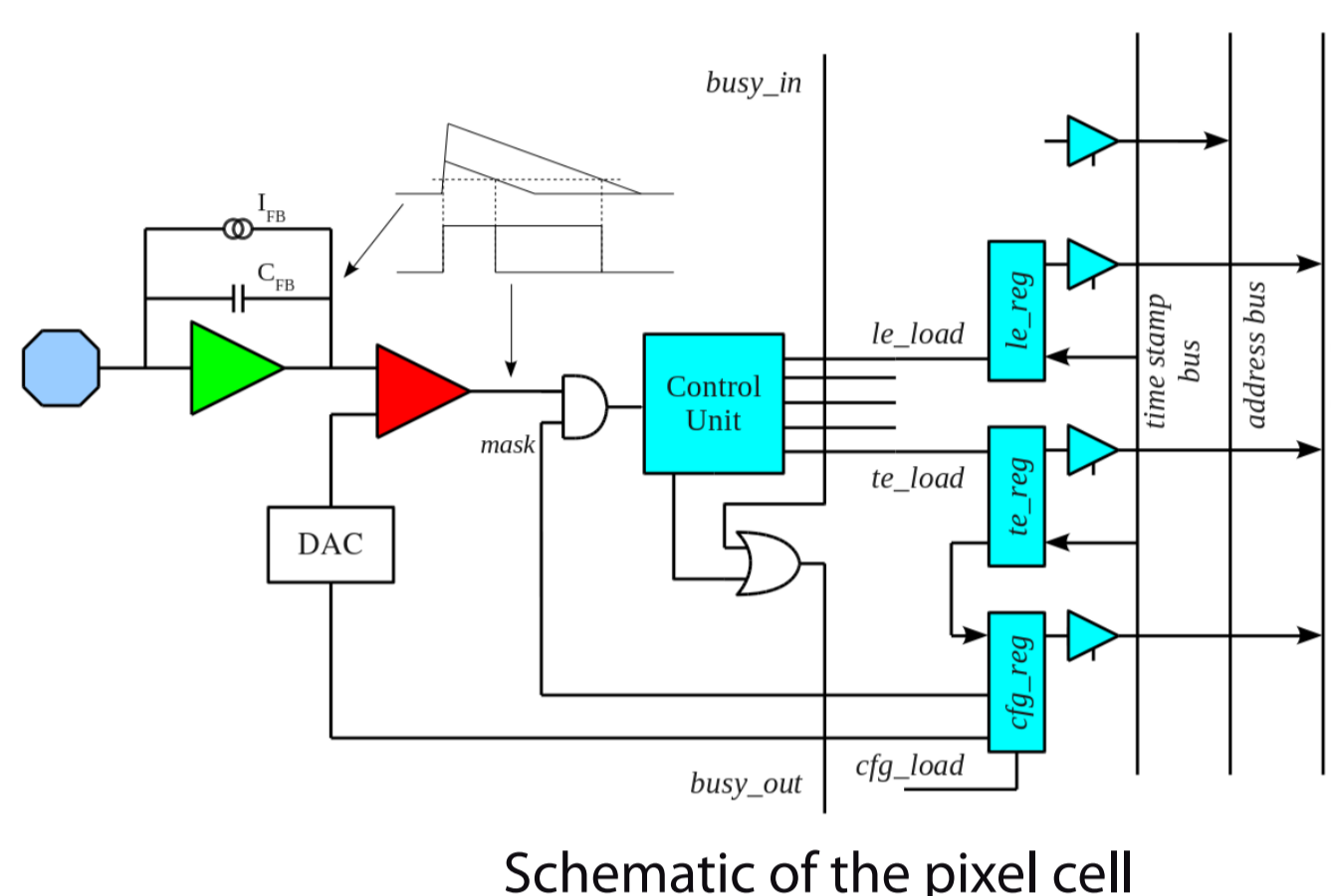
The Micro-Vertex-Detector

- 4 concentric barrels and 6 forward disks
- Vertex reconstruction for primary and secondary vertices
- Improvement of momentum resolution and PID
- Requirements:
 - spatial resolution (tens of μm)
 - good time resolution and low material budget
 - high radiation tolerance ($10^{14} n_{1\text{MeV eq}} / \text{cm}^2$)

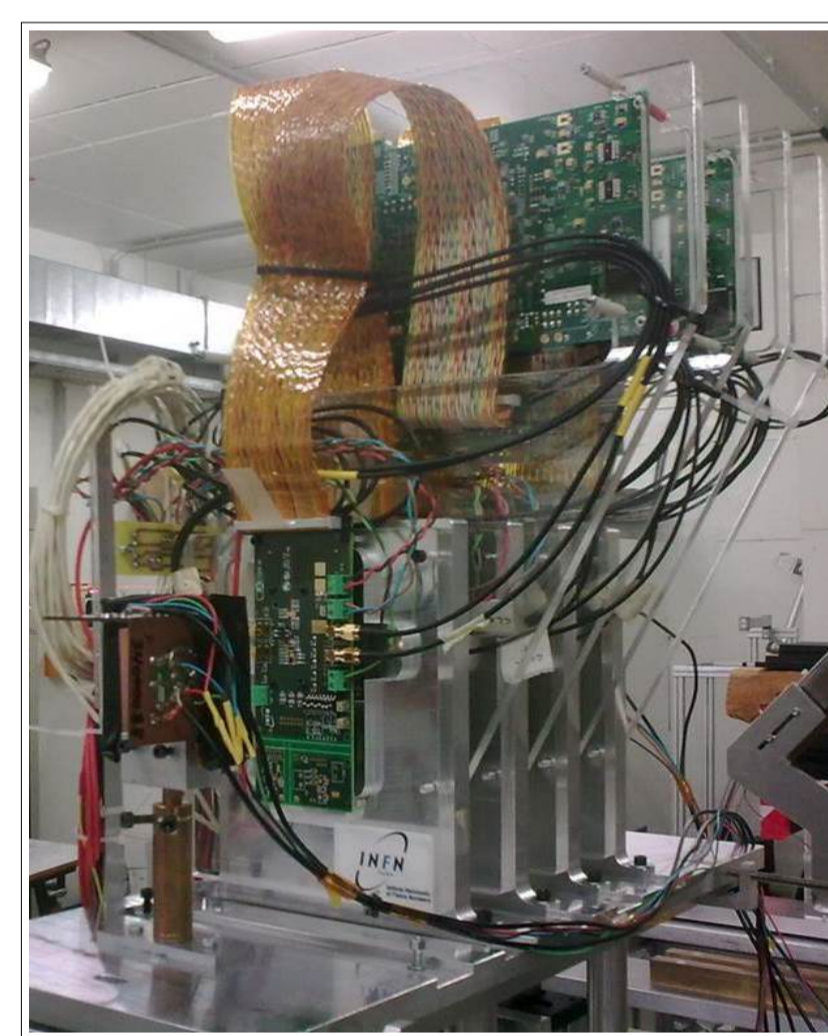


Hybrid Pixel Detector Readout: ToPix

- Detector modules based on epitaxial pixel sensors and ToPix readout chip
- Main features of ToPix:
 - pixel size: $100 \times 100 \mu\text{m}^2$
 - chip active area: $11.4 \times 11.6 \text{ mm}^2$ (116 rows, 110 columns)
 - dE/dx measurement: ToT, 12 bits dynamic range
 - Max. input charge: 50 fC
 - Noise floor: $< 200 e^-$
 - Input clock frequency: 160 MHz
 - Time resolution: 6.43 ns (1.86 ns r.m.s.)
 - Power consumption: $< 800 \text{ mW} / \text{cm}^2$
 - Max. event rate: $6.1 \cdot 10^6 / \text{s}$
 - Total Ionizing Dose: $< 100 \text{ kGy}$



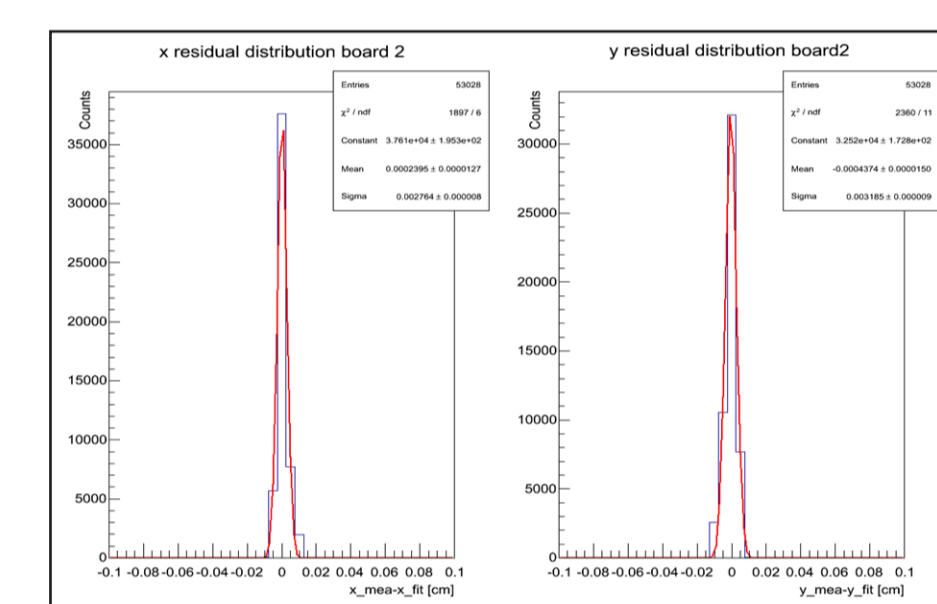
SEU tests of ToPix_v4 with ion beams @ LNL-INFN. Study of the configuration registers inside the pixels. SEU cross section one order of magnitude lower with respect to ToPix_v3 (D-type flip-flops circuits with TMR instead of latches with TMR)



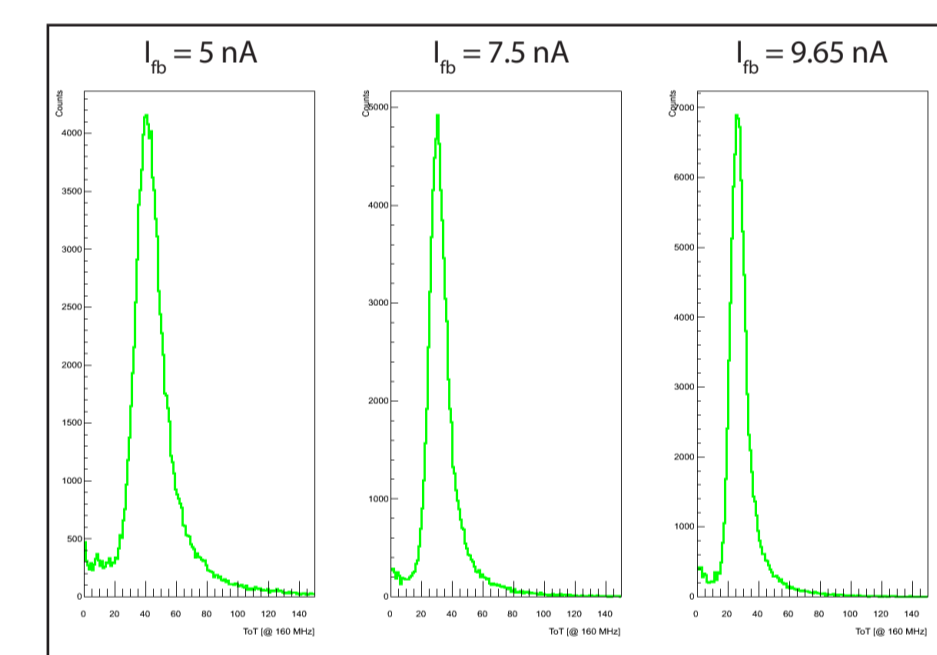
4 single-chip assemblies under test at FZJ with 2.9 GeV/c proton beam

ToPix_v4 prototype

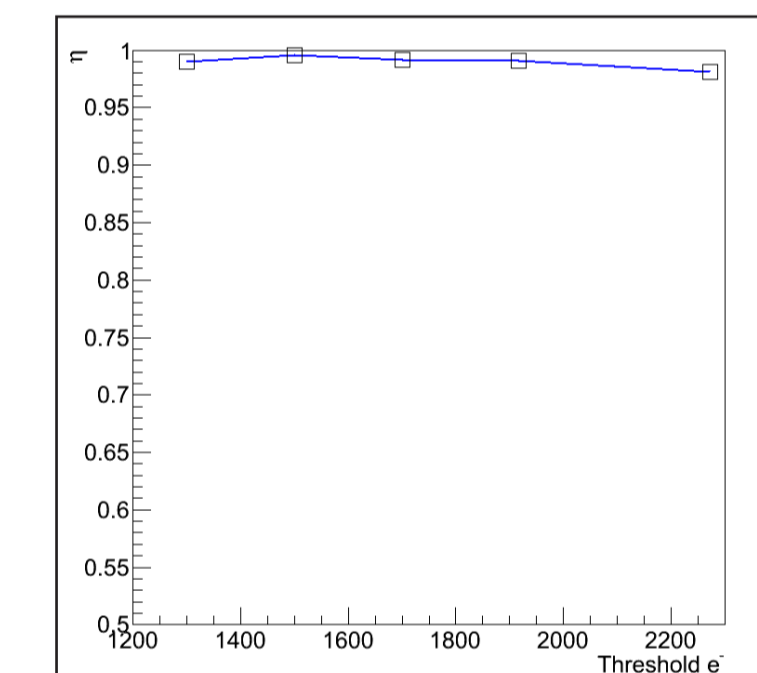
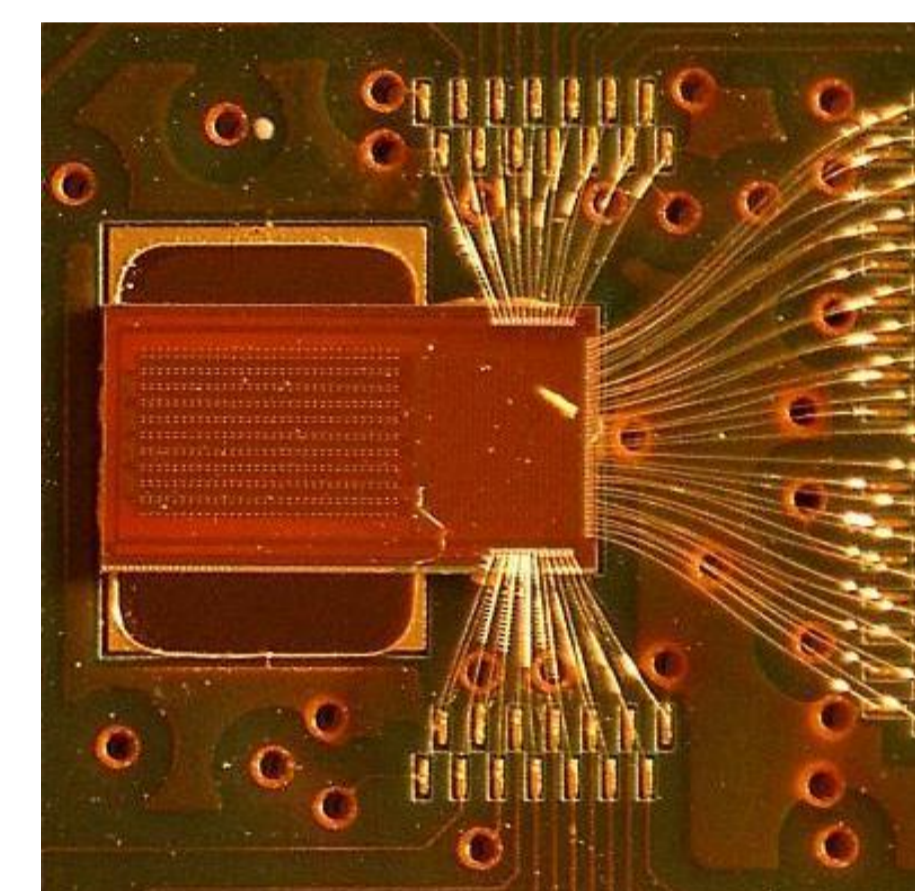
- ASIC size: $3 \times 6 \text{ mm}^2$, clock frequency 160 MHz
- 130 nm CMOS technology
- Pixel matrix: 640 cells, $2 \times 2 \times 128$ and $2 \times 2 \times 32$ columns
- Time over Threshold technique, 12 bits dynamic range
- Compatible with sensors of previous version (ToPix_v3)
- Hamming encoding and TMR pixel logic protection
- Leading and trailing edge registers with DICE-protected latches
- SEU protected EoC
- Serial data output (SDR and DDR)
- GBT compatible SLVS I/O



Residual distributions



ToT at several discharge currents of the feedback capacitor

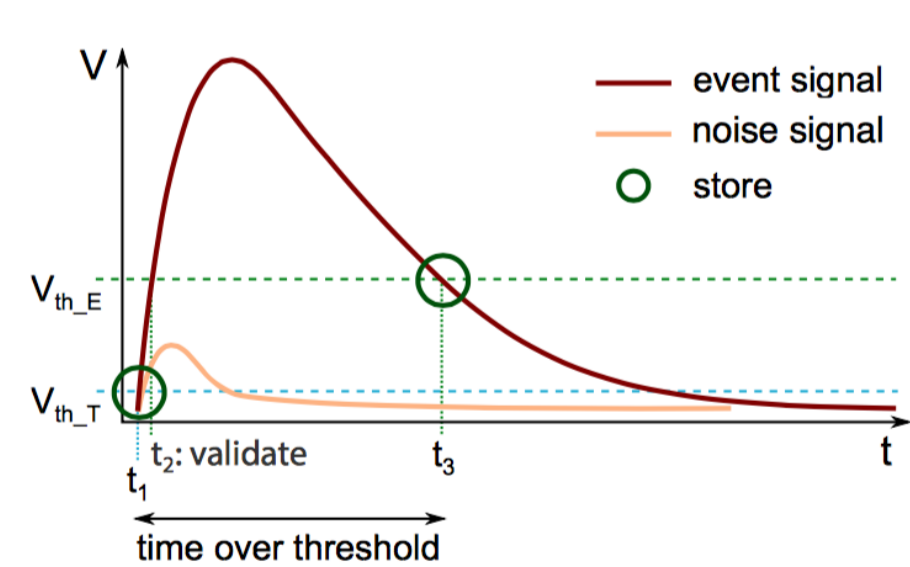


Efficiency vs. threshold

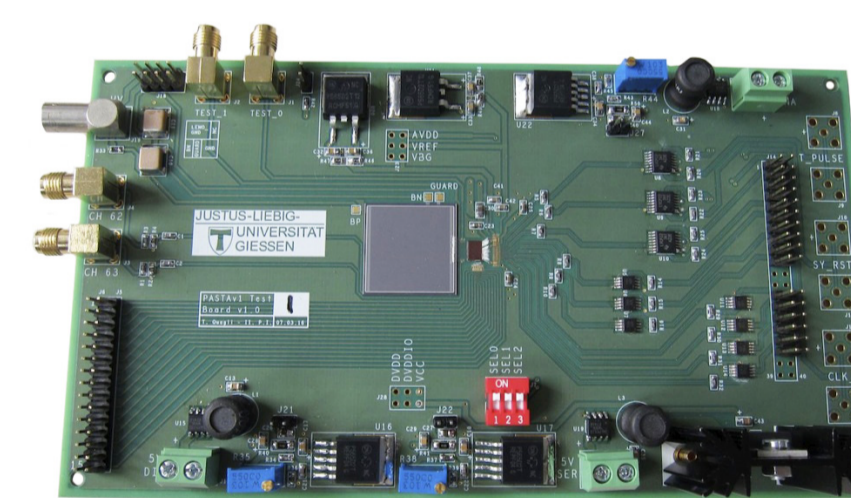
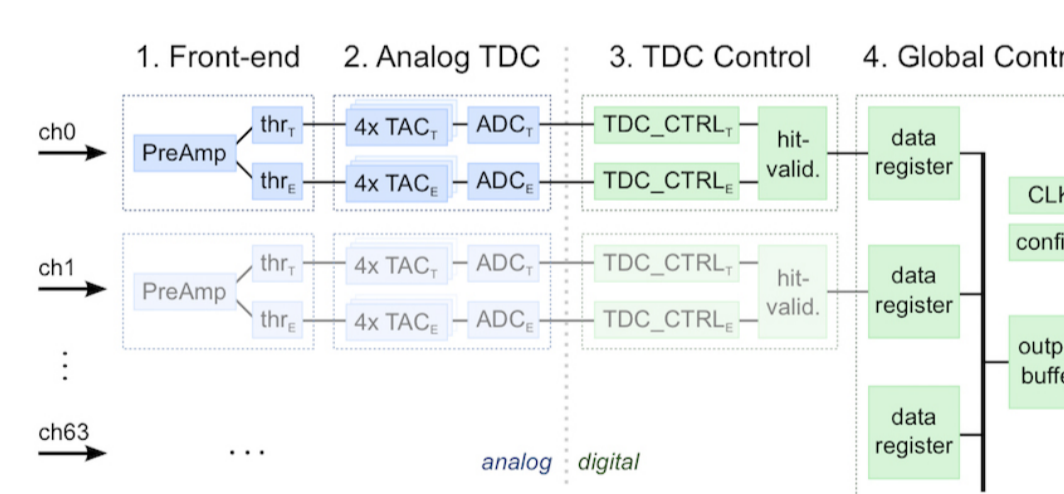
Double-sided Silicon Strip Detector Readout: PASTA

- Barrels: rectangular and square strip sensors
- Disks: trapezoidal strip sensors
- Front-end readout chip: PASTA (PANDA STRip ASIC)
- Chip concept inspired by TOPPET
- Main features of PASTA:
 - channels: 64
 - input pitch: $63 \mu\text{m}$
 - clock frequency: 160 MHz
 - rate capability: 100 kHz / ch
 - time bin width: 50 - 400 ps
 - dE/dx measurement: ToT, 8 bits dynamic range
 - Front-end noise: $< 600 e^-$
 - Power consumption: $< 4 \text{ mW} / \text{ch}$
 - Radiation tolerance: 100 kGy (TID)
 - Technology: CMOS 110 nm

Measurement Concept

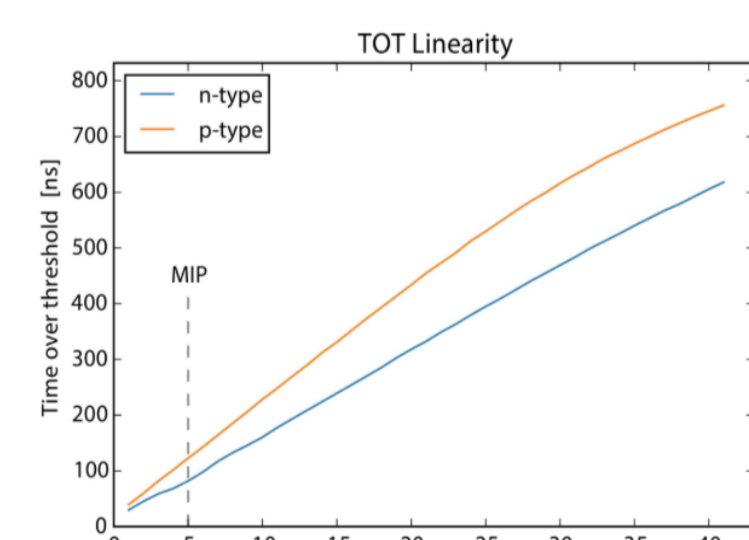


Chip Architecture

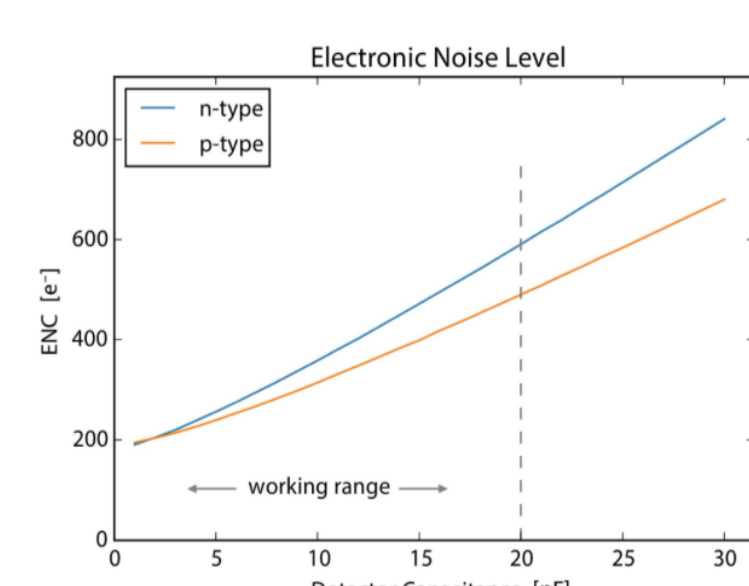


PASTA on the DISH (Digital Interface for Strip data Handling) test board with a strip sensor

Chip Simulations

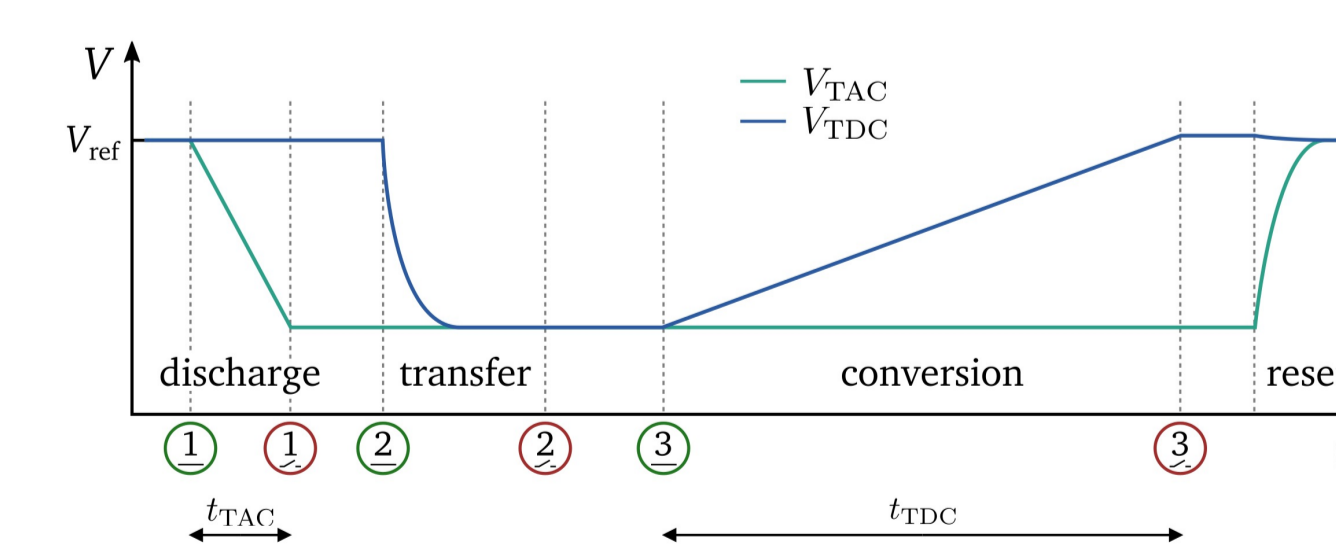
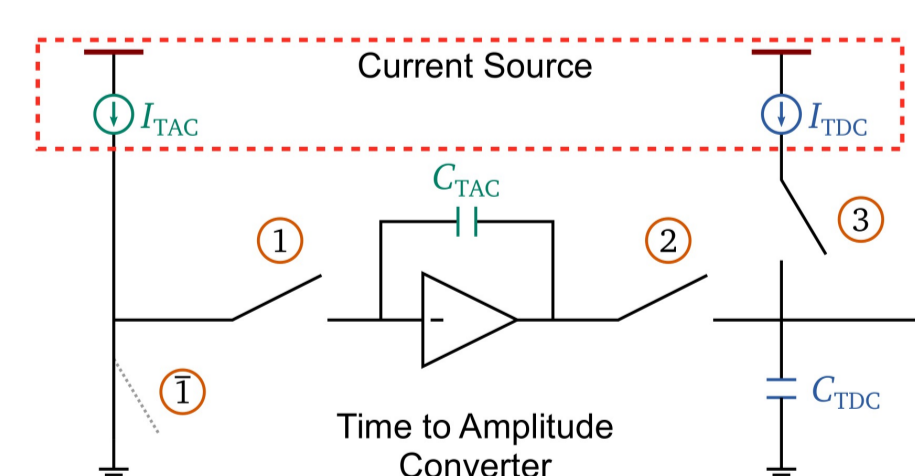


ToT linearity in the input charge range from 1 fC to 40 fC with a capacitance of 25 pF



Electronic noise with an input charge of 4 fC, for a capacitance from 1 pF to 30 pF

Analog TDC

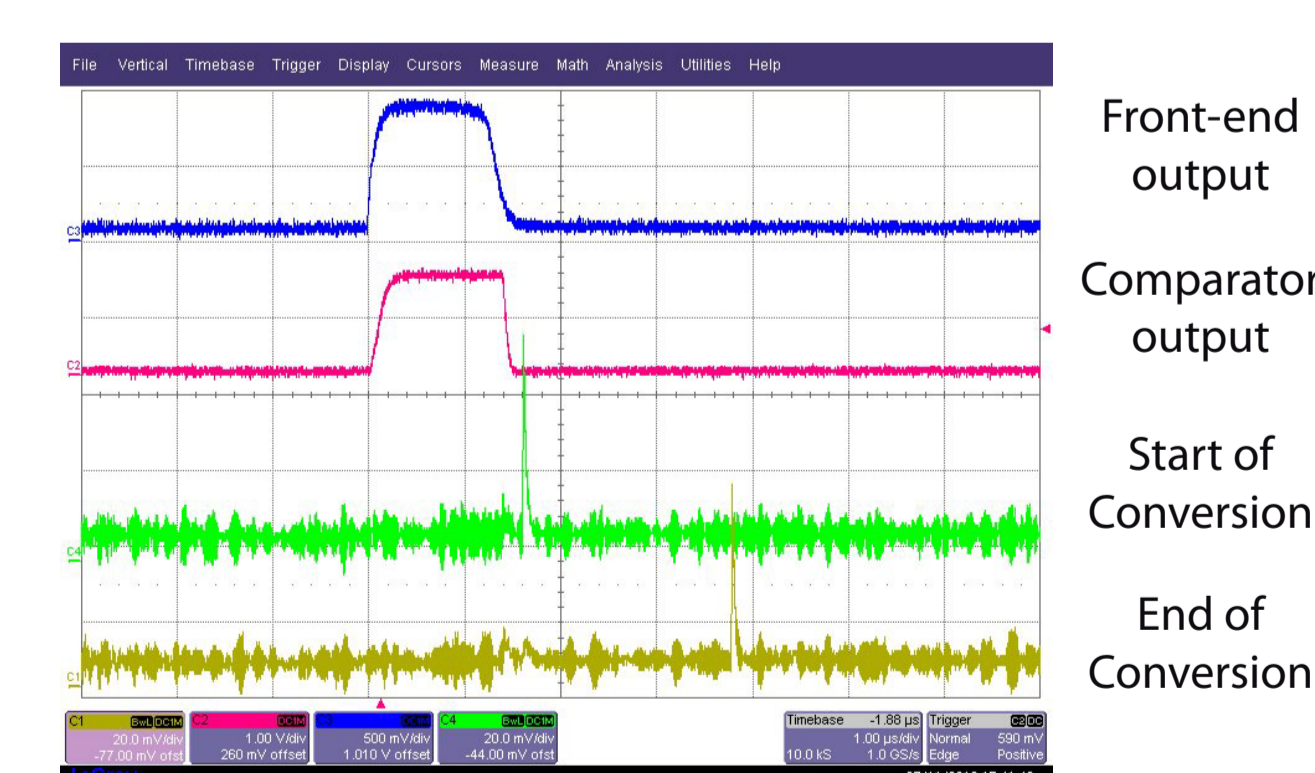


Analog TDC architecture and working principle

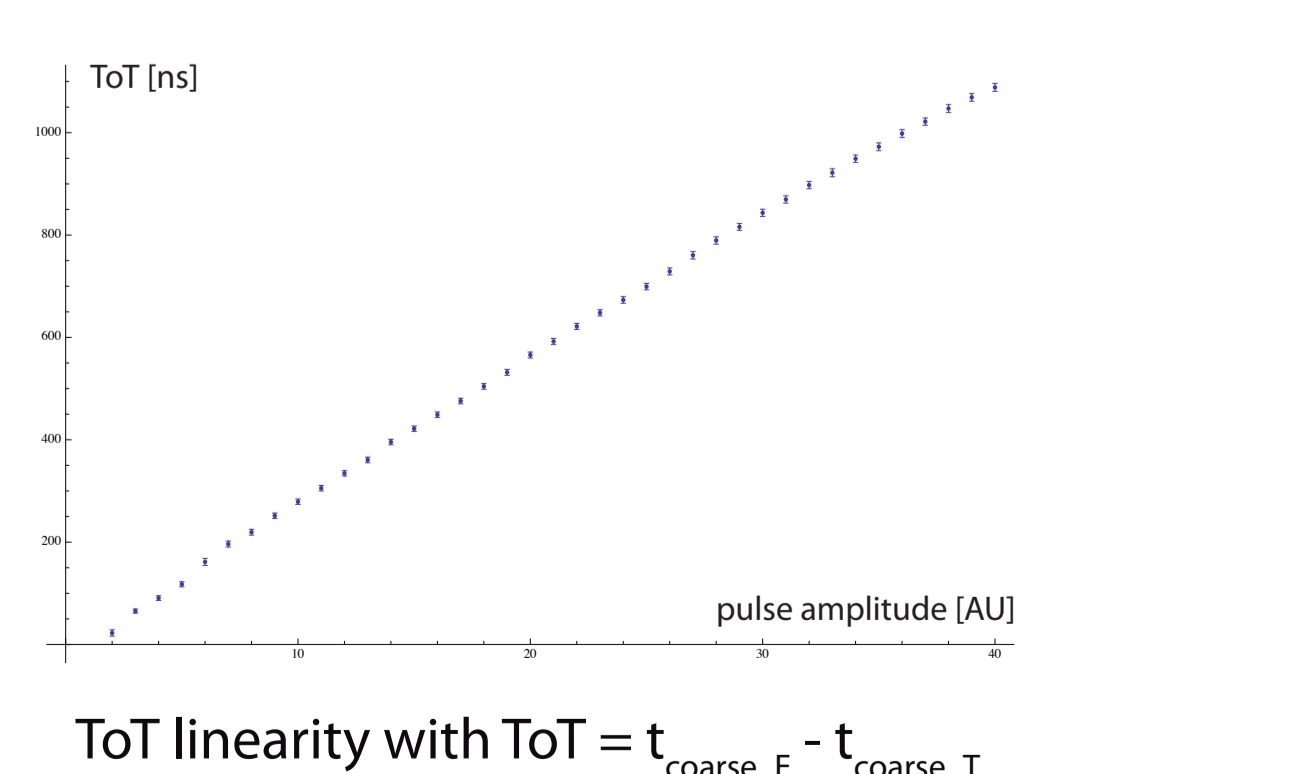
$$C_{TDC} = 4 \cdot C_{TAC}; I_{TDC} = 1/32 I_{TAC}$$

$$V_{TDC} = V_{TAC} \rightarrow t_{TDC} = 128 \cdot t_{TAC}$$

First test results



Example of chip test signals for an injected pulse



ToT linearity with $ToT = t_{coarse_E} - t_{coarse_T}$

